

1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state loss
- Low thermal resistance
- Rugged: reverse voltage surge capability
- Soft recovery minimizes power-consuming oscillations

3. Applications

- Output rectifiers in high-frequency switched-mode power supplies

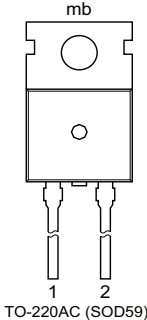
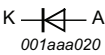
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute maximum rating							
V _{RRM}	repetitive peak reverse voltage		200				V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 128 °C; square-wave pulse; Fig. 1 ; Fig. 2	8				A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 128 °C; square-wave pulse	16				A
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse	80				A
		t _p = 8.3 ms; T _{j(init)} = 25 °C; sine-wave pulse	88				A
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _F	forward voltage	I _F = 8 A; T _J = 150 °C; Fig. 4		-	0.8	0.895	V
Dynamic characteristics							
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _J = 25 °C; ramp recovery; Fig. 5 ; Fig. 7		-	20	25	ns
Electrostatic discharge							
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	-	8	kV

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
mb	mb	mounting base; cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYW29E-200	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59

7. Marking

Table 4. Marking codes

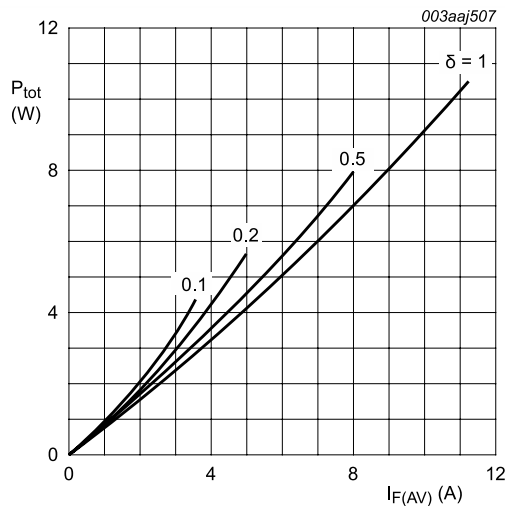
Type number	Marking codes
BYW29E-200	BYW29E-200

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

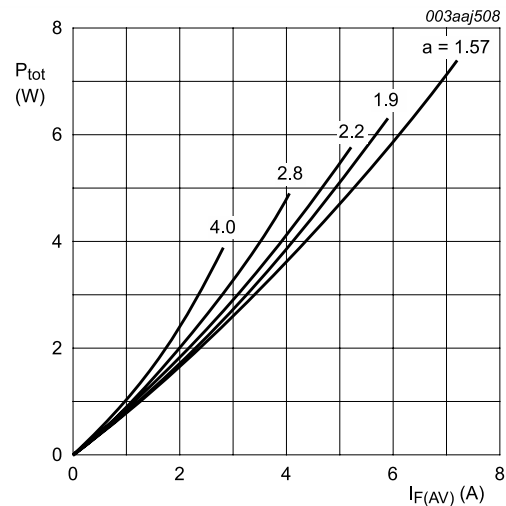
Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		200	V
V_{RWM}	crest working reverse voltage		200	V
V_R	reverse voltage		200	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $T_{mb} \leq 128^\circ\text{C}$; square-wave pulse; Fig. 1 ; Fig. 2	8	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25\ \mu\text{s}$; $T_{mb} \leq 128^\circ\text{C}$; square-wave pulse	16	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10\ \text{ms}$; $T_{j(\text{init})} = 25^\circ\text{C}$; sine-wave pulse	80	A
		$t_p = 8.3\ \text{ms}$; $T_{j(\text{init})} = 25^\circ\text{C}$; sine-wave pulse	88	A
I_{RRM}	repetitive peak reverse current	$\delta = 0.001$; $t_p = 2\ \mu\text{s}$	0.2	A
I_{RSM}	non-repetitive peak reverse current	$t_p = 100\ \mu\text{s}$	0.2	A
T_{stg}	storage temperature		-40 to 150	$^\circ\text{C}$
T_j	junction temperature		150	$^\circ\text{C}$
Electrostatic discharge				
V_{ESD}	electrostatic discharge voltage	HBM; $C = 250\ \text{pF}$; $R = 1.5\ \text{k}\Omega$	8	kV



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 0.791\ \text{V}; R_s = 0.013\ \Omega$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

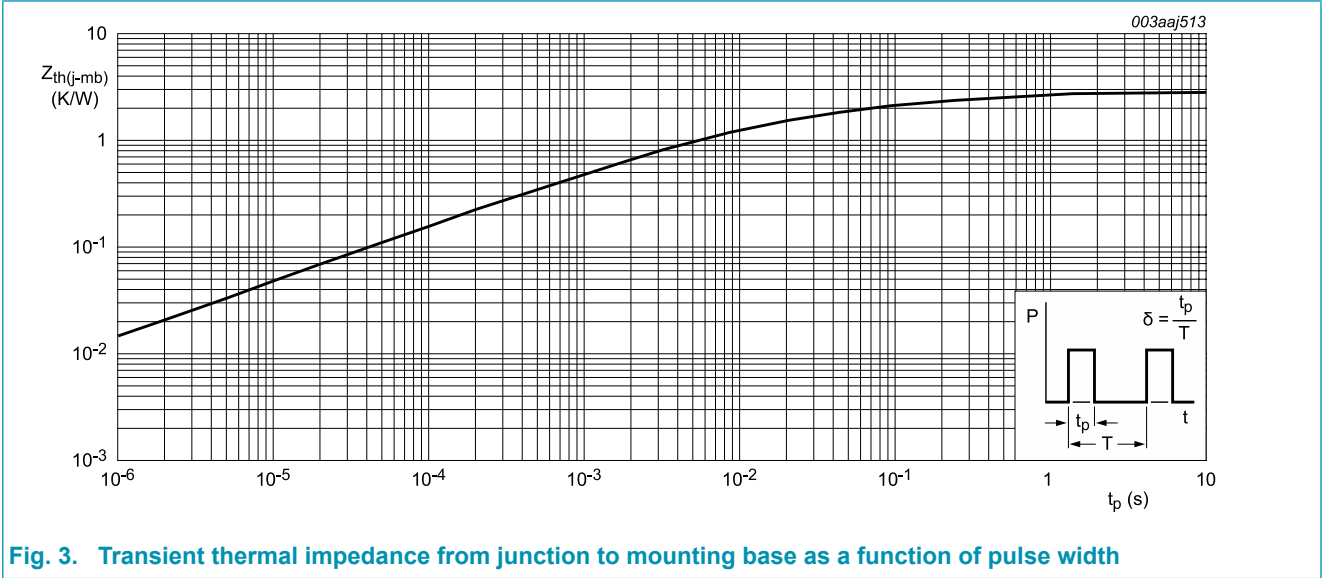
$$V_o = 0.791\ \text{V}; R_s = 0.013\ \Omega$$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

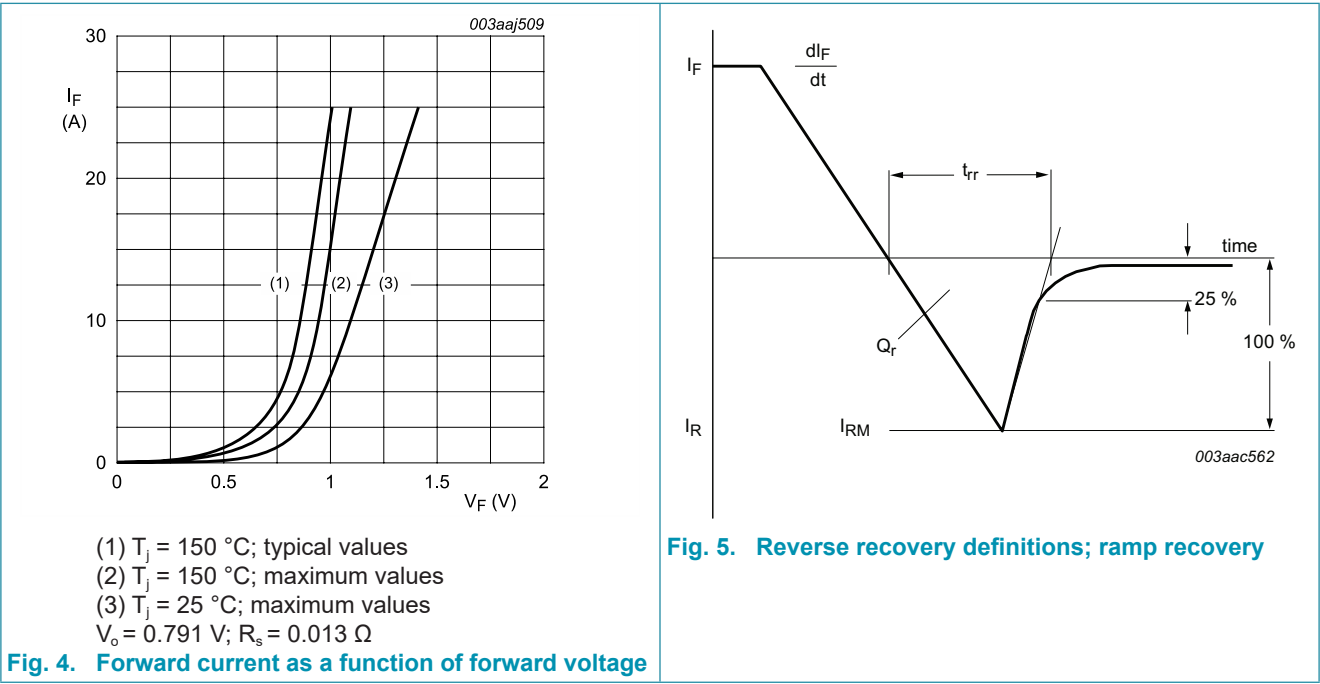
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 3		-	-	2.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W

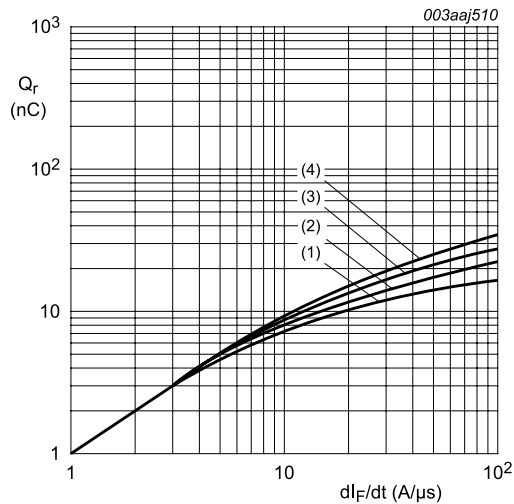


10. Characteristics

Table 7. Characteristics

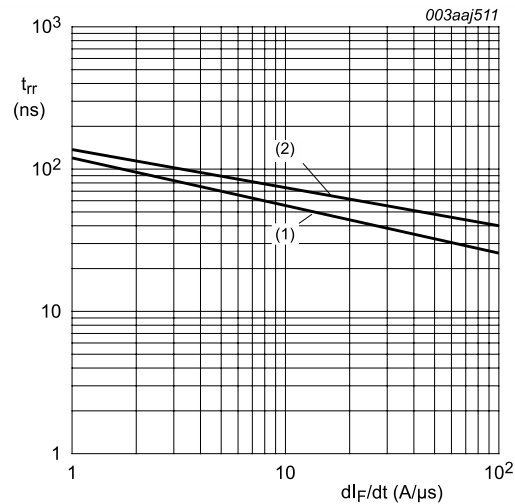
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; Fig. 4		-	0.92	1.05	V
		I _F = 20 A; T _j = 25 °C; Fig. 4		-	1.1	1.3	V
		I _F = 8 A; T _j = 150 °C; Fig. 4		-	0.8	0.895	V
I _R	reverse current	V _R = 200 V; T _j = 25 °C		-	2	10	μA
		V _R = 200 V; T _j = 100 °C		-	0.2	0.6	mA
Dynamic characteristics							
Q _r	recovered charge	I _F = 2 A; V _R = 30 V; dI _F /dt = 20 A/μs; T _j = 25 °C; Fig. 5 ; Fig. 6		-	4	11	nC
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _j = 25 °C; ramp recovery; Fig. 5 ; Fig. 7		-	20	25	ns
		I _F = 0.5 A; I _R = 1 A; I _{R(meas)} = 0.25 A; T _j = 25 °C; step recovery; Fig. 8		-	15	20	ns
V _{FRM}	forward recovery voltage	I _F = 1 A; dI _F /dt = 10 A/μs; T _j = 25 °C; Fig. 9		-	1	-	V





- (1) $I_F = 1\text{ A}; T_j = 25^\circ C$
- (2) $I_F = 2\text{ A}; T_j = 25^\circ C$
- (3) $I_F = 5\text{ A}; T_j = 25^\circ C$
- (4) $I_F = 10\text{ A}; T_j = 25^\circ C$

Fig. 6. Recovered charge as a function of rate of change of forward current; maximum values



- (1) $I_F = 1\text{ A}; T_j = 25^\circ C$
- (2) $I_F = 10\text{ A}; T_j = 25^\circ C$

Fig. 7. Reverse recovery time as a function of rate of change of forward current; maximum values

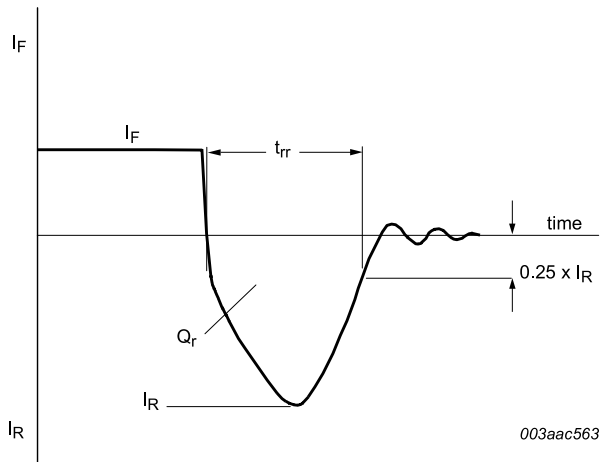


Fig. 8. Reverse recovery definitions; step recovery

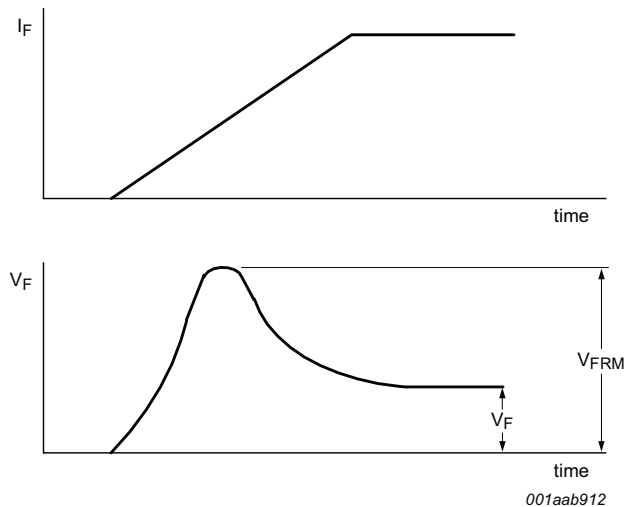
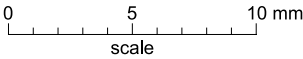
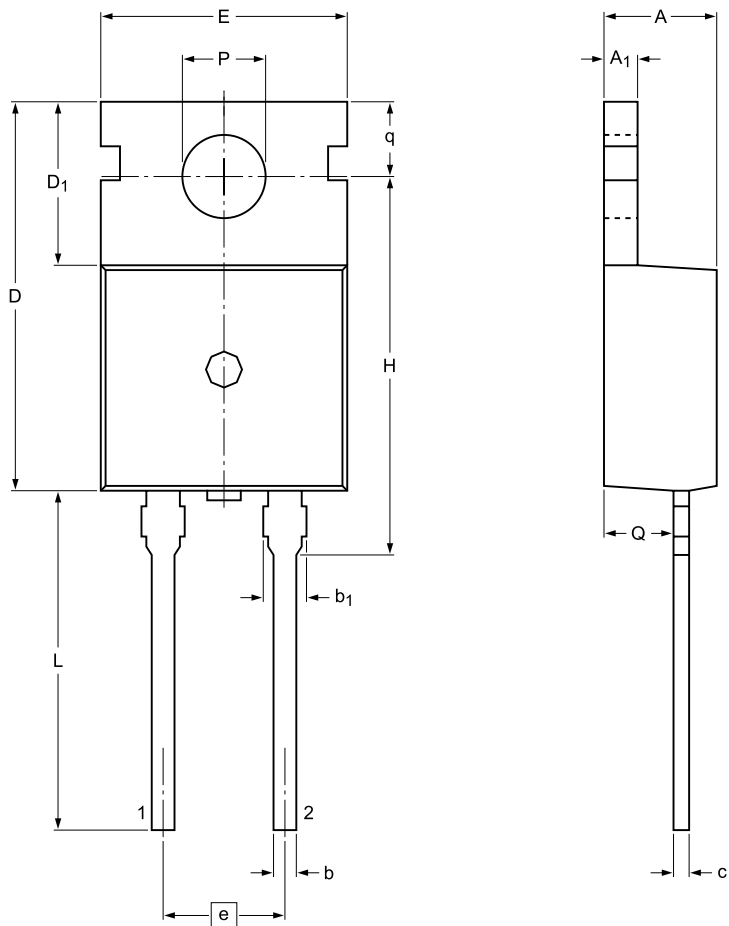


Fig. 9. Forward recovery definitions

11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC

SOD59



Dimensions

Unit		A	A ₁	b	b ₁ (¹)	c	D	D ₁	E	e	H	L	P	Q	q
mm	max	4.7	1.40	0.95	1.7	0.65	15.8	6.8	10.30	5.08 (REF)	16.25	15.0	3.80	2.6	2.9
	min	4.3	1.15	0.70	1.3	0.45	15.6	6.4	9.65		15.70	12.5	3.65	2.2	2.7

Note
1. Protruded dambar are included in the dimension.

sod059_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOD59	2-lead TO-220AC					09-08-25 12-11-27

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 4 June 2018



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